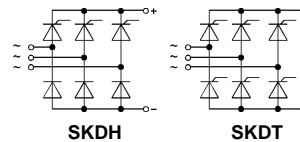
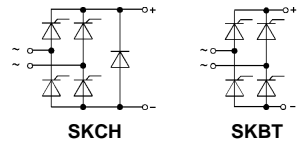


V <sub>DRM</sub> V <sub>RSM</sub> V <sub>RRM</sub> V	I <sub>D</sub> (T <sub>case</sub> = ... °C, full conduction)				
	40 A (92 °C)	40 A (92 °C)	100 A (84 °C)	60 A (86 °C)	100 A (84 °C)
400	<b>SKCH</b>	<b>SKBT</b>	<b>SKDH</b>	<b>SKDT</b>	<b>SKDT</b>
800	<b>40/04</b>	–	–	<b>60/04</b>	–
1200	<b>40/08</b>	<b>40/08</b>	<b>100/08</b>	<b>60/08</b>	<b>100/08</b>
1400	<b>40/12</b>	<b>40/12</b>	<b>100/12</b>	<b>60/12</b>	<b>100/12</b>
1600	<b>40/14</b>	<b>40/14</b>	<b>100/14</b>	<b>60/14</b>	<b>100/14</b>
1600	<b>40/16</b>	–	–	–	–

## SEMIPONT® 2 Controllable Bridge Rectifiers

**SKCH 40**      **SKDT 60**  
**SKBT 40**      **SKDT 100**  
**SKDH 100**



Symbol	Conditions	SKCH 40 SKBT 40	SKDT 60	SKDH 100 SKDT 100	Units
I <sub>D</sub>	T <sub>case</sub> = 85 °C; inductive load	46	61	98	A
	T <sub>amb</sub> = 45 °C, chassis <sup>1)</sup>	15	16	20	A
	P13A/125	18	21	25	A
	R4A/120	18			A
	P1A/120	28	34	45	A
T <sub>amb</sub> = 35 °C, P1A/120 F		47	57	85	A
	P3/180 F	55	65	95	A
I <sub>TSM</sub>	T <sub>vj</sub> = 25 °C, 10 ms	470	470	1000	A
	T <sub>vj</sub> = 125 °C, 10 ms	400	400	850	A
i <sup>2</sup> t	T <sub>vj</sub> = 25 °C, 8,3...10 ms	1100	1100	5000	A <sup>2</sup> s
	T <sub>vj</sub> = 125 °C, 8,3...10 ms	800	800	3600	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C, 50 Hz		50		A/μs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C, <sup>2</sup> / <sub>3</sub> V <sub>DRM</sub>		500		V/μs
I <sub>H</sub>	T <sub>vj</sub> = 25 °C, typ./max.		100/200		mA
I <sub>L</sub>	T <sub>vj</sub> = 25 °C, typ./max.		250/400		mA
V <sub>T</sub>	T <sub>vj</sub> = 25 °C; (I <sub>T</sub> = ...)	2,3 (75)	2,3 (75)	1,95 (200)	V A
V <sub>T(TO)</sub>	T <sub>vj</sub> = 125 °C	1,0	1,0	1,0	V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C	16	16	4,5	mΩ
I <sub>DD</sub> ; I <sub>RD</sub>	T <sub>vj</sub> = 125 °C; V <sub>DD</sub> = V <sub>DRM</sub> V <sub>RD</sub> = V <sub>RRM</sub>	10	10	15	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C, V <sub>D</sub> = 6 V		3		V
I <sub>GT</sub>	T <sub>vj</sub> = 25 °C, V <sub>D</sub> = 6 V		150		mA
V <sub>GD</sub>	T <sub>vj</sub> = 125 °C, V <sub>D</sub> = 6 V		0,25		V
R <sub>thjc</sub>	per thyristor/diode	1,0	1,0	0,85	°C/W
	total	0,25	0,167	0,141	°C/W
R <sub>thch</sub>	total		0,05		°C/W
T <sub>vj</sub> , T <sub>stg</sub>			– 40...+ 125		°C
V <sub>isol</sub>	a.c.50...60Hz;r.m.s.;1s/1min		3600 / 3000		V~
M <sub>1</sub>	to heatsink } SI (US) units		5 (44 lb.in.) ± 15 %		Nm
M <sub>2</sub>			3 (26 lb.in.) ± 15 %		Nm
w			165		g
Case	→ page B 11 – 67	G 19 G 20	G 21	G 21 G 53	

<sup>1)</sup> Painted metal sheet of minimum 250 x 250 x 1 mm: R<sub>thca</sub> = 1,8 °C/W

### Features

- Fully controlled single and three phase bridge rectifiers
- Robust plastic case with screw terminals
- Large, isolated base plate
- Blocking voltage to 1600 V
- High surge currents
- Easy chassis mounting
- UL recognized, file no. E 63 532

### Typical Applications

- SKCH, SKDH, SKDT for DC drives with a fixed direction of rotation
- SKBT, SKDT for reversing DC drives
- Controlled field rectifiers for DC motors
- Controlled battery charger rectifiers

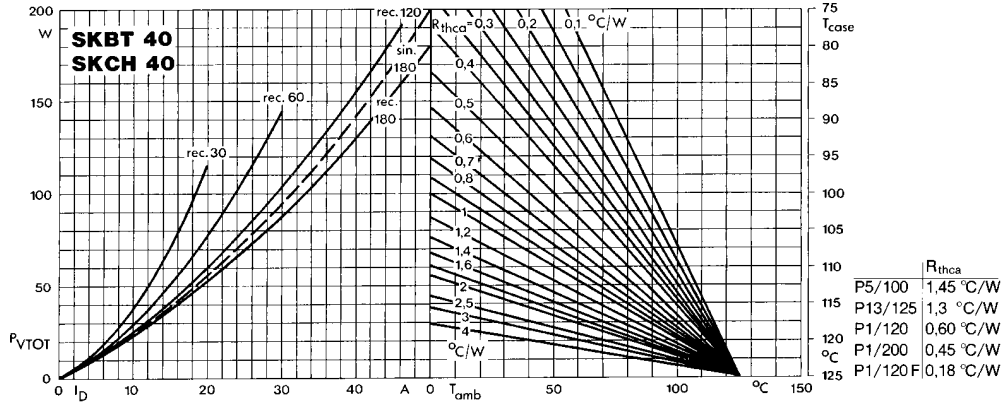


Fig. 4 a Power dissipation vs. output current and case temperature

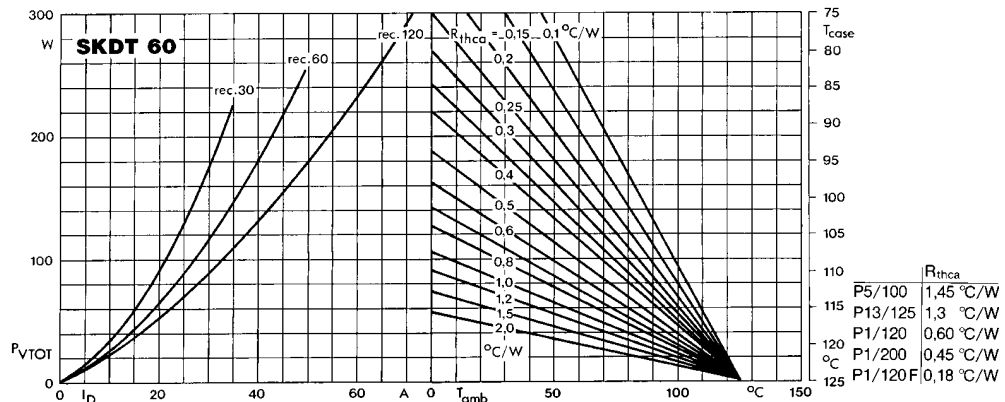


Fig. 4 b Power dissipation vs. output current and case temperature

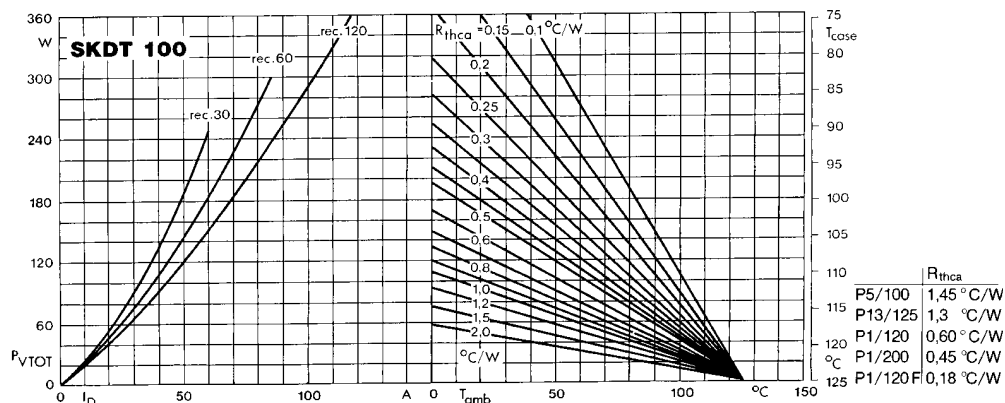


Fig. 4 c Power dissipation vs. output current and case temperature

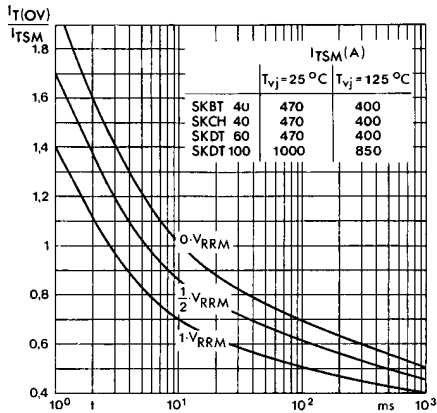


Fig. 5 Surge overload current vs. time

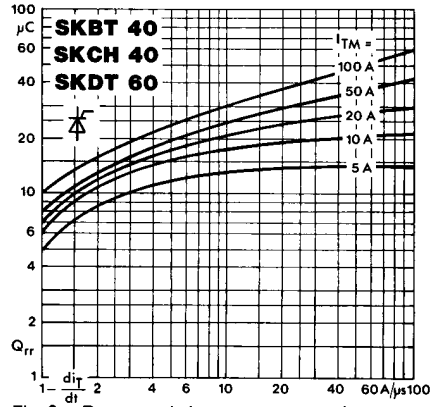


Fig. 8 a Recovered charge vs. current decrease

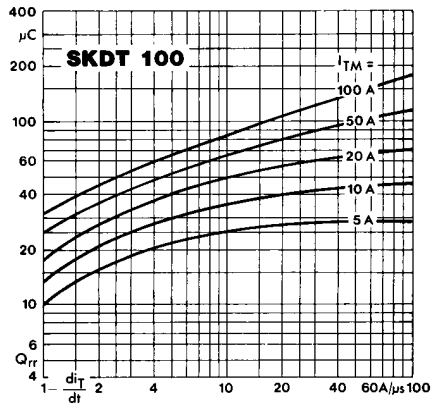


Fig. 8 b Recovered charge vs. current decrease

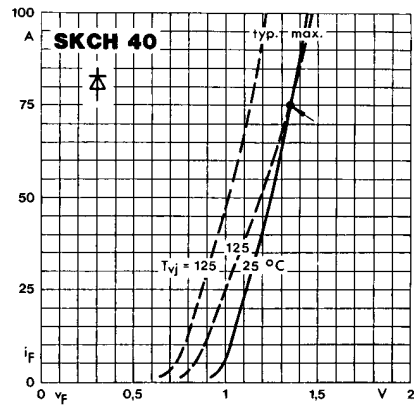


Fig. 9 Forward characteristics of a single diode

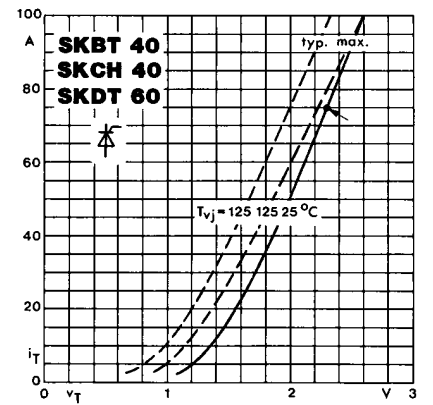


Fig. 10 a On-state characteristics of a single thyristor

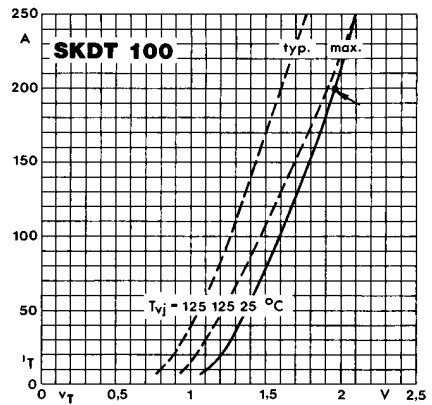


Fig. 10 b On-state characteristics of a single thyristor

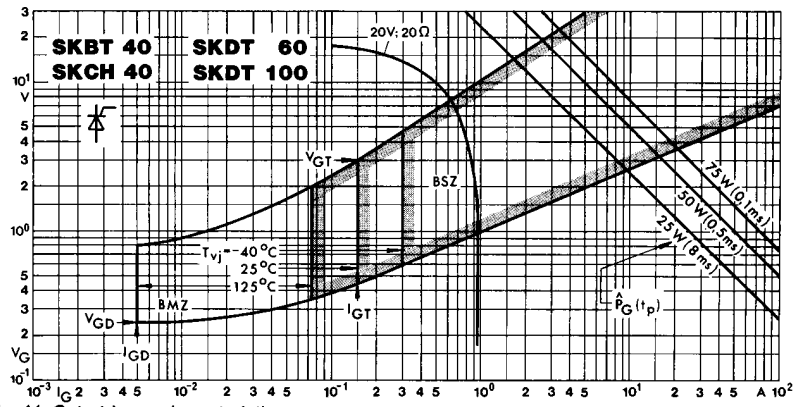


Fig. 11 Gate trigger characteristics

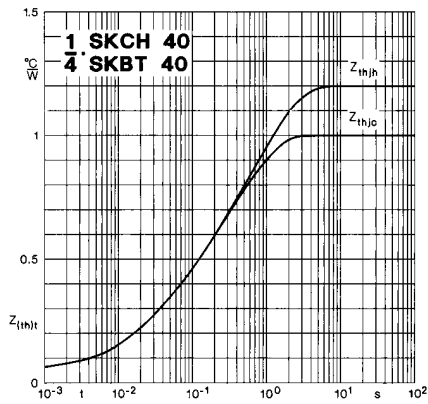


Fig. 12 a Transient thermal impedance vs. time

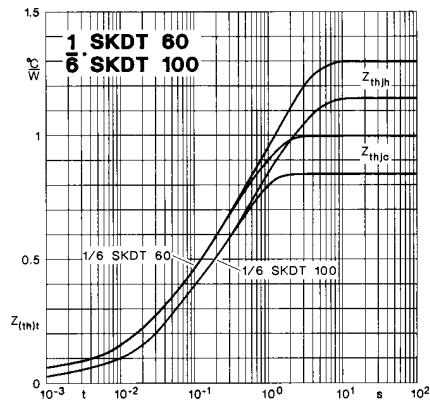
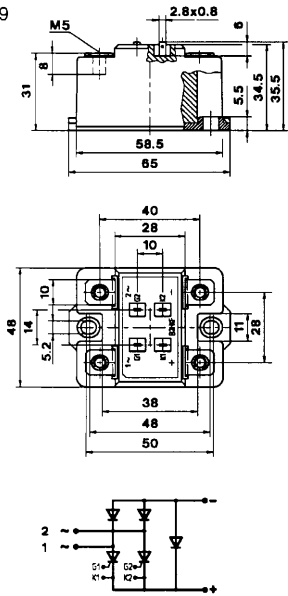


Fig. 12 b Transient thermal impedance vs. time

**SKCH 40** SEMIPONT® 2

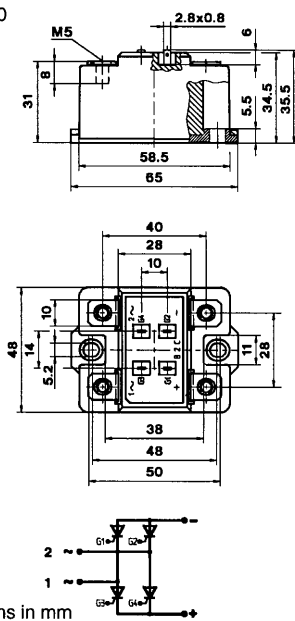
Case G 19



Dimensions in mm

**SKBT 40** SEMIPONT® 2

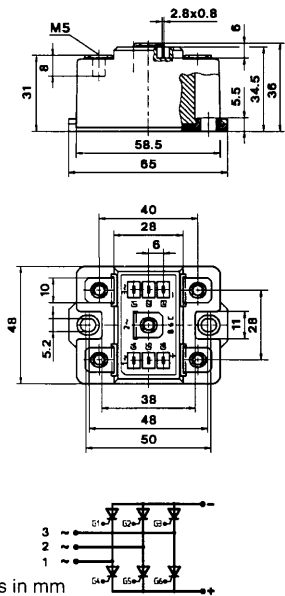
Case G 20



Dimensions in mm

**SKDT 60, SKDT 100** SEMIPONT® 2

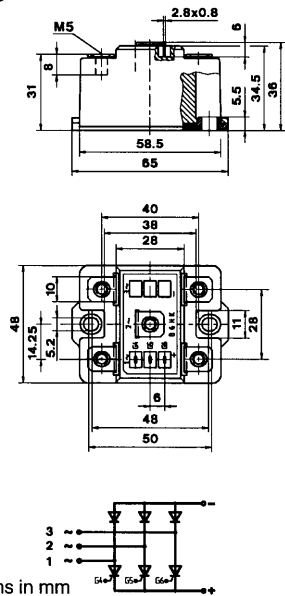
Case G 21



Dimensions in mm

**SKDL 100** SEMIPONT® 2

Case G 53



Dimensions in mm

### Available Heatsinks

Rectifier	Heatsink	w kg	R <sub>thca</sub> natural cooling °C/W	R <sub>thca</sub> forced cooling °C/W
SKB 15	P 5A/100	0,28	1,7	–
SKB 25, SKD 25	P 5A/100	0,28	1,55	–
	R 4A/120	0,6	1,45	–
	P 1/120	1,3	0,75	–
SKBH 28, SKBT 28, SKBZ 28, SKCH 28 SKB 30, SKD 30, SKD 31	P 5A/100	0,28	1,5	–
	R 4A/120	0,6	1,4	–
	P 1/120	1,3	0,7	–
	P13A/125	0,6	1,35	–
SKB 33, SKB 50, SKD 50	P1/120	1,3	0,65	0,30
SKBT 40, SKCH 40 SKB 60, SKD 60, SKDT 60 SKB 52, SKD 62, SKB 72 SKD 82, SKD 100, SKDT 100 SKD 110, SKD 160	P 5A/100	0,28	1,45	–
	R 4A/120	0,6	1,35	–
	P 13A/125	0,6	1,30	–
	P 15/180	1,7	0,8	0,30
	P 1/120	1,3	0,65	0,20
	P 3/180	3,1	0,5	0,18
	P 1/200	2,2	0,52	0,18

## Section 12: SEMISTACK<sup>®</sup> Thyristor, Rectifier Diode and IGBT Assemblies

### Summary of Types

Circuit <sup>1)</sup>	Page
<b>SEMISTACK<sup>®</sup> Converter Assemblies using thyristors and diodes <sup>2)</sup></b>	
<b>B2U</b> Non-controllable rectifier stacks in two-pulse bridge connection . . . . .	B 12 – 2
<b>B2HK, B2HK F</b> Half-controllable rectifier stacks in two-pulse bridge connection. . . . .	B 12 – 4
<b>B2C</b> Fully controllable converter-stacks in two-pulse bridge connection . . . . .	B 12 – 6
<b>B6U</b> Non-controllable rectifier stacks in six-pulse bridge connection . . . . .	B 12 – 8
<b>B6HK, B6HK F</b> Half-controllable rectifier stacks in six-pulse bridge connection . . . . .	B 12 – 10
<b>B6C</b> Fully controllable converter stacks in six-pulse bridge connection . . . . .	B 12 – 12
<b>(B6C)2, (B6C)2 I</b> Two inverse parallel six-pulse bridge connections for four-quadrant converters. . . . .	B 12 – 14
<b>W1C</b> Single phase a.c. controller stacks . . . . .	B 12 – 16
<b>W3C2</b> Three-phase a.c. controller stacks with two control elements only. . . . .	B 12 – 18
<b>W3C</b> Three-phase a.c. controller stacks . . . . .	B 12 – 20
<b>E1U</b> Free wheeling diodes . . . . .	B 12 – 23
<b>SEMISTACK<sup>®</sup> IGBT Converter Assemblies using SEMITRANS<sup>®</sup> IGBTs and SKiiPPACK<sup>®</sup></b>	
<b>B6C I</b> Fully controllable PWM inverter stacks in six-pulse bridge configuration . . . . .	B 12 – 24
<b>SKiiP<sup>®</sup></b> Assemblies (examples). . . . .	B 12 – 26
<b>Drawings of the assemblies</b> Fig. 1 to Fig. 44 . . . . .	B 12 – 29
<b>Checklist for SEMISTACK<sup>®</sup> and SKiiP / Fax cover page</b> . . . . .	B 12 – 55
<b>Checkliste für SEMISTACK<sup>®</sup> und SKiiP / Fax-Deckblatt für Anfrage</b> . . . . .	B 12 – 59
<b>SEMISTACK<sup>®</sup> R</b> Rotating silicon rectifier assemblies in six-pulse bridge connection for brushless a.c. generators . . . . .	B 12 – 63

**This is our standard SEMISTACK<sup>®</sup> program. Most of the assemblies above are also offered mounted on water-cooled heatsinks. Numerous special designs may be supplied according to the customer's demand. Our application engineers are available to propose the most reliable and cost-effective solution to your needs.**

**Please contact your nearest SEMIKRON sales office.**

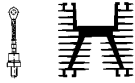
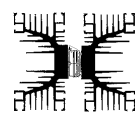
#### Notes

<sup>1)</sup> IEC 971 - 1989-07: 4.1 ... 4.3


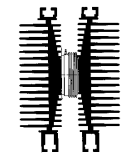
<sup>2)</sup> RC-snubber circuits, semiconductor fuses, varistors and bimetal thermal trips appropriate to each SEMISTACK<sup>®</sup> are offered on request.

## Discrete rectifier diodes with non-isolated heatsinks

Natural cooling;  $T_{amb} \leq 45\text{ °C}$

	Code Designation * $V_{VRMS} / V_D - I_d$ $V / V - A$	Device Type	Heatsink Type / L mm	Thermal Trip °C	Overall Dimensions			Outline Figure
					Height mm	Width mm	Depth mm	
	<b>B2U... / ...-100</b>	<b>SKN 100</b>	<b>C3/120</b>		120	234	130	12 a
	-165	SKN/R 100	P1/150		150	375	250	15 a
	-190	SKN/R 130	P1/200		200	375	250	15 b
	-275	SKN/R 240	P1/200		200	375	250	15 b
	-350	SKN/R 240	P1/400		400	375	250	15 c
	-430	SKN/R 320	P1/400		400	375	250	15 c
	-490	SKN/R 320	P4/400		400	475	270	19 a
	-600	SKN 501	P11/415		635	500	275	21 a
	-645	SKN 870	P11/415		635	500	275	21 a
	-845	SKN 870	U3/515		740	560	290	25 a
	-1090	SKN 1500	U3/515		740	560	290	25 a

Forced air cooling;  $T_{amb} \leq 35\text{ °C}$

	<b>B2U... / ...-245 F</b>	<b>SKN/R 100</b>	<b>P1/150</b>	85	208	375	250	15 a
	-310 F	SKN/R 130	P1/200	85	258	375	250	15 b
	-485 F	SKN/R 240	P1/200	100	258	375	250	15 b
	-545 F	SKN/R 240	P1/400	95	458	375	250	15 c
	-675 F	SKN/R 320	P1/400	100	458	375	250	15 c
	-885 F	SKN 501	P18/130	112	558	382	344	28 a
	-1200 F	SKN 870	P18/130	112	558	382	344	28 b
	-1525 F	SKN 1500	P18/130	132	558	406	344	28 b
	-1865 F	SKN 2000	P18/130	132	558	406	344	28 b
	-1970 F	SKN 1500	N4/250	118	790	542	400	34
	-2560 F	SKN 2000	N4/250	118	790	542	400	34

\*) see page A – 96: siehe Seite A – 221